

L Number	Hits	Search Text	DB	Time stamp
1	0	semiconductor adj laser adj chip and resin and wavelength near6 "1.096"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/20 12:55
2	0	semiconductor adj laser adj chip and resin and wavelength near6 "1.069"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/20 12:56
3	0	semiconductor adj laser and wavelength near6 "1.069"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/20 12:56
4	505	semiconductor adj laser and carbon adj dioxide and wavelength	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/20 12:56
5	0	semiconductor adj laser and carbon adj dioxide and wavelength near6 ".mu.m"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/20 12:56
6	13	semiconductor adj laser and carbon adj dioxide and wavelength near6 micron	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/20 12:59
7	335	semiconductor adj laser and wavelength near6 micron	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/20 13:07
8	147	semiconductor adj laser.ti,ab,clm. and wavelength near6 micron	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/20 13:08
9	0	semiconductor adj laser.ti,ab,clm. and wavelength near6 micron and transparent near2 resin	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/20 13:08
10	4	semiconductor adj laser.ti,ab,clm. and wavelength near6 micron and resin	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/20 13:20
11	1	semiconductor adj laser.ti,ab,clm. and GaAs adj diode and resin and wavelength	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/20 14:21
12	5334	((372/43) or (372/44) or (372/45) or (372/46) or (372/47) or (372/48) or (372/49) or (372/50)).CCLS.	USPAT; US-PGPUB	2004/06/20 14:26
13	39	((372/43) or (372/44) or (372/45) or (372/46) or (372/47) or (372/48) or (372/49) or (372/50)).CCLS.) and protect\$3 and eye	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/20 14:31
14	5	(US-6654399-\$ or US-5745515-\$).did. or (US-20030035460-\$ or US-20030035461-\$ or US-20020154667-\$).did.	USPAT; US-PGPUB	2004/06/20 14:31
15	0	((US-6654399-\$ or US-5745515-\$).did. or (US-20030035460-\$ or US-20030035461-\$ or US-20020154667-\$).did.) and protect\$3 near10 eye and diffus\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/20 14:32

16	0	((US-6654399-\$ or US-5745515-\$).did. or (US-20030035460-\$ or US-20030035461-\$ or US-20020154667-\$).did.) and protect\$3 near10 eye	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB	2004/06/20 14:32
17	597	(372/44).CCLS.	USPAT; US-PGPUB	2004/06/20 14:59
18	999	(372/43).CCLS.	USPAT; US-PGPUB	2004/06/20 14:59
19	877	((372/43).CCLS.) not ((372/44).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB	2004/06/20 15:00
20	11	(US-5422905-\$ or US-5488678-\$ or US-5373519-\$ or US-5105237-\$ or US-5907571-\$ or US-5734672-\$ or US-5758951-\$ or US-6144684-\$ or US-6654399-\$).did. or (US-20030035460-\$ or US-20030035461-\$).did.	USPAT; US-PGPUB	2004/06/20 15:03
21	182	((372/29.01) or (372/29.014)).CCLS.	USPAT; US-PGPUB	2004/06/20 15:08
22	17	((372/29.01) or (372/29.014)).CCLS.) and eye	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2004/06/20 15:08
23	2	(US-5383200-\$ or US-5394419-\$).did.	USPAT	2004/06/20 15:12
24	2	((US-5383200-\$ or US-5394419-\$).did.) and eye	USPAT	2004/06/20 15:12
-	2	("4829531").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2004/06/20 12:55
-	2	("4829531").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2002/10/31 16:31
-	2	("5488678").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2002/10/31 16:35
-	2	("5825952").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2002/10/31 16:33
-	0	jp-04449242\$--.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2002/10/31 16:36
-	1	jp-04249442\$--.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2002/10/31 16:39
-	0	jp-02511591\$--.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2002/10/31 16:38
-	7	"511591"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/10/31 16:38

-	2742	resin near6 silica near6 epoxy	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/01 16:34
-	6327	molded adj resin near (resin near6 silica near6 epoxy) epoxy near15 silica	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/01 16:34
-	109	molded adj resin near (resin near6 silica near6 epoxy) epoxy near15 silica and laser.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/01 16:34
-	7	molded adj resin near (resin near6 silica near6 epoxy) (mixture or mixed) near15 epoxy near15 silica and laser.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/01 17:38
-	7	(seal or molded) adj resin near (resin near6 silica near6 epoxy) (mixture or mixed) near15 epoxy near15 silica and laser.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/01 17:39
-	29	(seal or molded) near3 resin near (resin near6 silica near6 epoxy) (mixture or mixed) near15 epoxy near15 silica and laser.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/01 18:08
-	20	jp-0818163\$-\$ did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/01 18:09
-	0	jp-0818163\$-\$ did. and double adj sealing	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/01 18:09
-	116	double adj sealing and resin	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/01 18:09
-	23	double adj sealing near12 resin	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/01 18:24
-	1977	(mixing or mix or mixture) near12 resin and (light adj emitting or light-emitting or laser).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/01 18:26
-	14	(mixing or mix or mixture) near12 resin near12 refractive adj index and (light adj emitting or light-emitting or laser).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/01 19:06
-	19	(thermal adj resistance or heat adj capacity) near15 (chip or die) and laser.ti,ab,clm. and (372/\$6.cccls. or 257/\$6.cccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/01 19:22
-	0	(thermal adj resistance or heat adj capacity) near15 (chip or die) and heat adj sink near15 (contain or container) and laser.ti,ab,clm. and (372/\$6.cccls. or 257/\$6.cccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/01 19:24

-	0	(thermal adj resistance or heat adj capacity) near15 (chip or die) and heat adj sink near15 (contain or container) and laser.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 19:24
-	26	(thermal adj resistance or heat adj capacity) near15 (chip or die) and heat adj sink near15 (contain or container)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 19:25
-	170	(372/4\$1.cccls. or 372/50.cccls.) and thermal adj resistance	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/02 10:34
-	2	(372/4\$1.cccls. or 372/50.cccls.) and (thermal adj resistance near15 "deg/W")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/02 10:37
-	2	(372/4\$1.cccls. or 372/50.cccls.) and "deg/W"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/02 10:37
-	2	(372/4\$1.cccls. or 372/50.cccls. or 257/79.cccls. or 257/8\$1.cccls. or 257/9\$1.cccls. or 257/100.cccls. or 257/101.cccls. or 257/102.cccls. or 257/103.cccls.) and "deg/W"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/02 10:40
-	3654	(372/4\$1.cccls. or 372/50.cccls. or 257/79.cccls. or 257/8\$1.cccls. or 257/9\$1.cccls. or 257/100.cccls. or 257/101.cccls. or 257/102.cccls. or 257/103.cccls.) and ("deg/W" or (thermal resistance near12 heat sink))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/02 10:41
-	2868	(372/4\$1.cccls. or 372/50.cccls. or 257/79.cccls. or 257/8\$1.cccls. or 257/9\$1.cccls. or 257/100.cccls. or 257/101.cccls. or 257/102.cccls. or 257/103.cccls.) and ("deg/W" or (thermal resistance near12 heat adj sink))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/02 10:42
-	2867	(372/4\$1.cccls. or 372/50.cccls. or 257/79.cccls. or 257/8\$1.cccls. or 257/9\$1.cccls. or 257/100.cccls. or 257/101.cccls. or 257/102.cccls. or 257/103.cccls.) and ("deg/W" or (thermal resistance near6 heat adj sink))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/02 10:43
-	365	(372/4\$1.cccls. or 372/50.cccls. or 257/79.cccls. or 257/8\$1.cccls. or 257/9\$1.cccls. or 257/100.cccls. or 257/101.cccls. or 257/102.cccls. or 257/103.cccls.) and ("deg/W" or (low near6 thermal resistance near6 heat adj sink))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/02 10:43
-	2	(372/4\$1.cccls. or 372/50.cccls. or 257/79.cccls. or 257/8\$1.cccls. or 257/9\$1.cccls. or 257/100.cccls. or 257/101.cccls. or 257/102.cccls. or 257/103.cccls.) and ("deg/W" or (low near6 thermal near6 resistance near6 heat adj sink))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/02 10:44
-	1	(372/4\$1.cccls. or 372/50.cccls. or 257/79.cccls. or 257/8\$1.cccls. or 257/9\$1.cccls. or 257/100.cccls. or 257/101.cccls. or 257/102.cccls. or 257/103.cccls.) and ((low or lower) near6 thermal near6 resistance near6 heat adj sink)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/02 10:46

-		19	(372/4\$ccls. or 372/50.ccls. or 257/79.ccls. or 257/8\$1.ccls. or 257/9\$1.ccls. or 257/100.ccls. or 257/101.ccls. or 257/102.ccls. or 257/103.ccls.) and (thermal adj resistance near6 heat adj sink)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/02 10:49
-		1	thermal adj resistance near3 copper near12 "deg/W"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/02 12:17
-		9	(thickness or thick) near4 heat adj sink and (257/\$6.ccls. or 372/\$6.ccls.) and (area near4 bonded)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/02 11:19
-		25	(US-5307362-\$ or US-5373519-\$ or US-5422905-\$ or US-6448583-\$ or US-6049423-\$ or US-5105237-\$ or US-5970081-\$ or US-5734672-\$ or US-6219364-\$ or US-6049125-\$ or US-5758951-\$ or US-6133631-\$ or US-6144684-\$ or US-4829531-\$ or US-5488678-\$ or US-5825952-\$ or US-5907571-\$ or US-5355385-\$).did. or (DE-4315581-\$).did. or (JP-61176169-\$ or JP-05129730-\$).did. or (EP-257898-\$ or JP-07045811-\$ or JP-09127349-\$ or EP-483549-\$).did.	USPAT; EPO; JPO; DERWENT	2002/11/02 11:53
-		0	heat adj sink near12 "W/deg" and (laser or light-emitting or light adj emitting).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/02 12:18
-		0	heat adj sink near12 "W/deg" and (laser or light-emitting or light adj emitting).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/02 12:18
-		0	heat adj sink near12 "W/deg" and (257/\$6.ccls. or 438/\$6.ccls. or 372/\$6.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/02 12:19
-		193	heat adj sink near12 thermal adj resistance and (257/\$6.ccls. or 438/\$6.ccls. or 372/\$6.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/02 12:20
-		43	heat adj sink near12 thermal adj resistance near12 low and (257/\$6.ccls. or 438/\$6.ccls. or 372/\$6.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/02 12:36
-		1	heat adj sink near12 thermal adj resistance near12 low near12 (copper or cu) and (257/\$6.ccls. or 438/\$6.ccls. or 372/\$6.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/02 12:22
-		43	heat adj sink near12 thermal adj resistance near12 low and (257/\$6.ccls. or 438/\$6.ccls. or 372/\$6.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/02 12:23
-		0	heat adj sink near12 thermal adj resistance near12 low near12 "K/W" and (257/\$6.ccls. or 438/\$6.ccls. or 372/\$6.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/02 12:37

	0	heat adj sink near12 thermal adj resistance near12 "K/W" and (257/\$6.cccls. or 438/\$6.cccls. or 372/\$6.cccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/02 12:38
-	0	heat adj sink near12 (copper or cu) near12 thermal adj resistance near12 "K/W"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/02 12:39
-	27	(US-5825952-\$ or US-6049125-\$ or US-6219364-\$ or US-6448583-\$ or US-5422905-\$ or US-5970081-\$ or US-5734672-\$ or US-6144684-\$ or US-6133631-\$ or US-5758951-\$ or US-6049423-\$ or US-4829531-\$ or US-5488678-\$ or US-4899210-\$ or US-5373519-\$ or US-5307362-\$ or US-5105237-\$ or US-5907571-\$ or US-5355385-\$ or US-5381859-\$).did. or (DE-4315581-\$).did. or (JP-61176169-\$ or JP-05129730-\$).did. or (JP-09127349-\$ or EP-257898-\$ or JP-07045811-\$ or EP-483549-\$).did.	USPAT; EPO; JPO; DERWENT	2002/11/02 13:46
-	2	monochromatic near12 laser adj diode adj array	USPAT; EPO; JPO; DERWENT	2002/11/02 13:47
-	5	laser adj diode adj array near12 "same wavelength"	USPAT; EPO; JPO; DERWENT	2002/11/02 17:01
-	4	(mqw or multiple adj quantum adj well) near6 different adj wavelength	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/02 18:59
-	2	("6049125").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/02 19:32
-	2	("6049423").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/02 19:37
-	14	((("6049423") or ("6049125") or ("5625402") or ("5422905") or ("5970081") or ("5355385") or ("5907571"))).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/02 19:37
-	7	((("6049423") or ("6049125") or ("5625402") or ("5422905") or ("5970081") or ("5355385") or ("5907571"))).PN.	USPAT	2002/11/02 19:38
-	2	semiconductor.ti,ab,clm. and laser.ti,ab,clm. and resin near12 (mixture or mix or mixing or mixed) near12 diffusion	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/11 16:03
-	6	laser.ti,ab,clm. and resin near12 (mixture or mix or mixing or mixed) near12 diffusion	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/11 16:07
-	3	laser.ti,ab,clm. and (light-diffusing or light adj diffusing) near3 resin	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/11 16:08

-	6	laser.ti,ab,clm. and (light-diffusing or light adj diffusing) near5 resin	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/11 16:09
-	34	(US-5614338-\$ or US-5530780-\$ or US-5976175-\$ or US-5307362-\$ or US-5355385-\$ or US-5105237-\$ or US-5373519-\$ or US-5970081-\$ or US-6133631-\$ or US-6144684-\$ or US-5734672-\$ or US-6448583-\$ or US-5422905-\$ or US-4899210-\$ or US-5625402-\$ or US-5758951-\$ or US-6219364-\$ or US-6049423-\$ or US-5488678-\$ or US-5825952-\$ or US-4829531-\$ or US-5907571-\$ or US-6049125-\$ or US-5381859-\$).did. or (US-20030031917-\$).did. or (DE-4315581-\$).did. or (JP-04037487-\$ or JP-61176169-\$ or JP-05129730-\$).did. or (GB-2142441-\$ or JP-07045811-\$ or JP-09127349-\$ or EP-257898-\$ or EP-483549-\$).did.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/13 17:38
-	18	(diffuse or diffusive) near12 resin and laser.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/13 18:01
-	0	eye near12 protect\$3 and laser.ti,ab,clm. and resin near12 diffus\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/13 18:03
-	0	eye near12 protect\$3 and laser.ti,ab,clm. and resin near12 (light-diffus\$3 or diffus\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/13 18:03
-	156	laser.ti,ab,clm. and resin near12 (light-diffus\$3 or diffus\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/13 18:03
-	4	laser.ti,ab,clm. and resin near12 light-diffus\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/13 18:13
-	34	laser.ti,ab,clm. and resin near12 (light near5 diffus\$3 or light-diffus\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/13 18:21
-	115	semiconductor adj laser.ti,ab,clm. and resin near6 lens	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/13 18:25
-	62	semiconductor adj laser.ti,ab,clm. and resin near3 lens	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/13 18:25
-	0	semiconductor adj laser.ti,ab,clm. and light-diffus\$3 near6 resin near3 lens	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/13 18:26
-	1	semiconductor adj laser.ti,ab,clm. and (light near3 diffus\$3 or light-diffus\$3) near6 resin near6 lens	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/13 18:28
-	1	semiconductor adj laser.ti,ab,clm. and (light near6 diffus\$3 or light-diffus\$3) near12 resin near6 lens	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/13 18:29
-	1	semiconductor.ti,ab,clm. and laser.ti,ab,clm. and (light near6 diffus\$3 or light-diffus\$3) near12 resin near6 lens	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/13 18:34

-	3	semiconductor.ti,ab,clm. and (light-emitting laser).ti,ab,clm. and (light near6 diffus\$3 or light-diffus\$3) near12 resin near6 lens	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/13 18:34
-	126	resin near6 lens and semiconductor adj2 laser.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/14 10:18
-	66	resin near3 lens and semiconductor adj2 laser.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/14 10:21
-	0	light-diffusive near6 resin near3 lens and semiconductor adj2 laser.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/14 10:19
-	0	(light near6 (diffusive or diffusion or diffuse) or light-diffusive) near6 resin near3 lens and semiconductor adj2 laser.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/14 10:20
-	0	(light near12 (diffusive or diffusion or diffuse) or light-diffusive) near12 resin near12 lens and semiconductor adj2 laser.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/14 10:21
-	34	resin near2 lens and semiconductor adj2 laser.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/14 10:22
-	0	molded near2 resin near2 lens and semiconductor adj2 laser.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/14 10:22
-	7	molded near12 resin near2 lens and semiconductor adj2 laser.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/14 10:28
-	2	laser.ti,ab,clm. and light-diffusive near6 resin	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/14 10:30
-	16	laser.ti,ab,clm. and (light near3 (diffusive or diffusion or diffuse) light-diffusive) near6 resin	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/14 14:40
-	1	jp-07072311\$--.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/14 14:41
-	2	("5976175").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/14 14:56
-	0	("761240.ap.").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/14 14:56

	4	761240.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/14 14:56
	11	"5177753"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/18 17:38
	2	("5177753").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/18 17:38
	4	667775.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/19 16:50
	2	("5386428").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/19 17:26
	2	("5970081").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/19 18:21
	2	("5422905").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/19 18:43
	2	("4870652").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/19 18:45
	0	("dualnear2lasernear2beamssamewavelength").PN	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/19 18:45
	14	dual near2 laser near2 beams same wavelength	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/19 18:57
	0	multiple adj beam adj semiconductor adj laser and "same wavelengths"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/19 18:58
	19	multiple adj beam adj semiconductor adj laser	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/19 18:58
	6	multiple adj beam adj semiconductor adj laser and wavelengths	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/19 19:46
	0	multiple adj beam adj semiconductor adj laser and different adj wavelengths	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/19 19:47

